# 74LVTN16245B

3.3 V 16-bit transceiver; 3-state

Rev. 5 — 5 April 2012

Product data sheet

# **General description**

The 74LVTN16245B is a high-performance BiCMOS product designed for V<sub>CC</sub> operation at 3.3 V.

This device is a 16-bit transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions. The control function implementation minimizes external timing requirements. The device features an output enable input (nOE) for easy cascading and a direction input (nDIR) for direction control.

#### **Features and benefits** 2.

- 16-bit bus interface
- 3-state buffers
- Output capability: +64 mA and -32 mA
- TTL input and output switching levels
- Input and output interface capability to systems at 5 V supply
- Power-up 3-state
- Live insertion and extraction permitted
- No bus current loading when output is tied to 5 V bus
- Latch-up protection
  - ◆ JESD78B Class II exceeds 500 mA
- ESD protection:
  - ♦ HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V

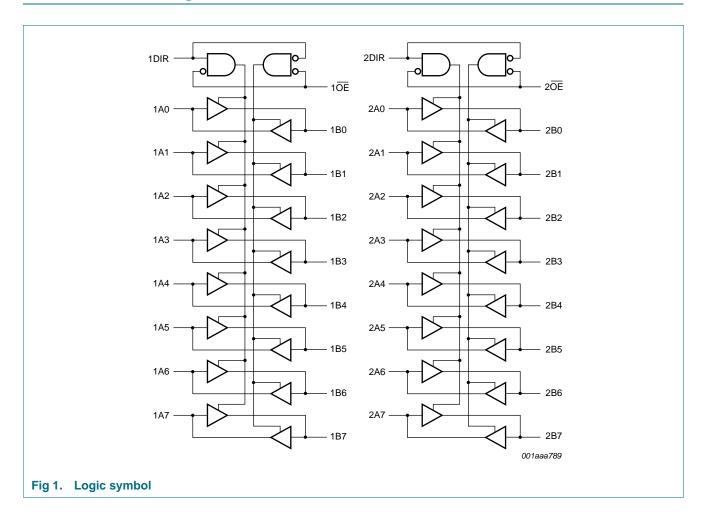
# **Ordering information**

Table 1. **Ordering information** 

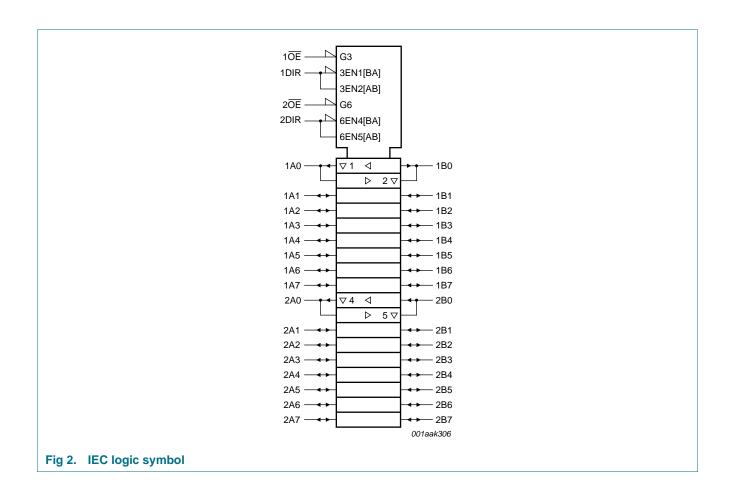
Type number	Package							
	Temperature range	Name	Description	Version				
74LVTN16245BDGG	-40 °C to +85 °C	TSSOP48	plastic thin shrink small outline package; 48 leads; body width 6.1 mm	SOT362-1				
74LVTN16245BBX	–40 °C to +125 °C	HXQFN60	plastic compatible thermal enhanced extremely thin quad flat package; no leads; 60 terminals; body 4 $\times$ 6 $\times$ 0.5 mm	SOT1134-2				



# 4. Functional diagram



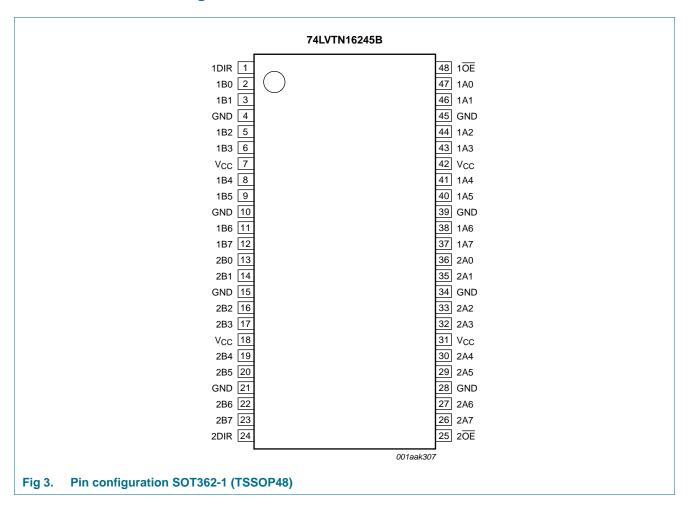
2 of 17



3 of 17

# 5. Pinning information

### 5.1 Pinning



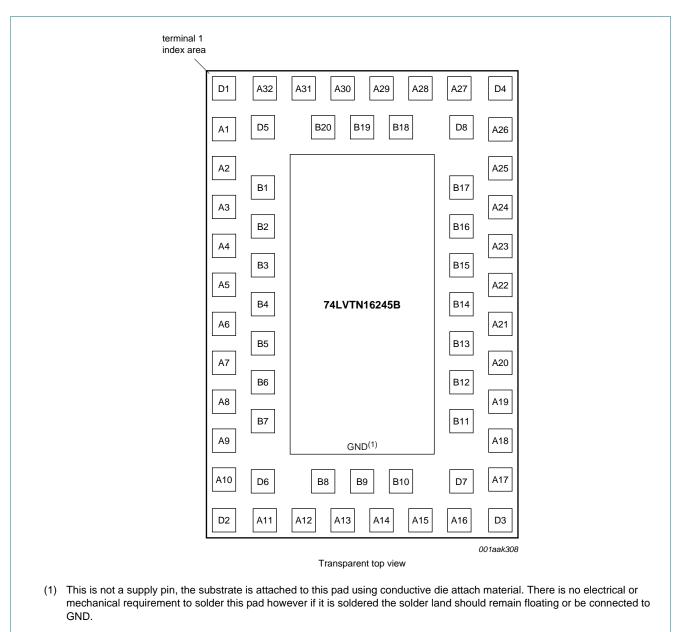


Fig 4. Pin configuration SOT1134-2 (HXQFN60)

### 5.2 Pin description

Table 2. Pin description

Symbol	Pin		Description
	SOT362-1	SOT1134-2	_
1DIR, 2DIR	1, 24	A30, A13	direction control input
1B0 to 1B7	2, 3, 5, 6, 8, 9, 11, 12	B20, A31, D5, D1, A2, B2, B3, A5	data input/output
2B0 to 2B7	13, 14, 16, 17, 19, 20, 22, 23	A6, B5, B6, A9, D2, D6, A12, B8	data input/output
GND	4, 10, 15, 21, 28, 34, 39, 45	A32, A3, A8, A11, A16, A19, A24, A27	ground (0 V)
$V_{CC}$	7, 18, 31, 42	A1, A10, A17, A26	supply voltage
10E, 20E	48, 25	A29, A14	output enable input (active LOW)
2A0 to 2A7	36, 35, 33, 32, 30, 29, 27, 26	A21, B13, B12, A18, D3, D7, A15, B10	data input/output
1A0 to 1A7	47, 46, 44, 43, 41, 40, 38, 37	B18, A28, D8, D4, A25, B16, B15, A22	data input/output
n.c.	-	A4, A7, A20, A23, B1, B4, B7, B9, B11, B14, B17, B19	not connected

# 6. Functional description

Table 3. Function table [1]

		Input/output		
nOE nDIR		nAn	nBn	
L	L	output nAn = nBn	input	
L	Н	input	output nBn = nAn	
Н	X	Z	Z	

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+4.6	V
VI	input voltage		<u>[1]</u> –0.5	+7.0	V
V <sub>O</sub>	output voltage	output in OFF-state or HIGH-state	<u>[1]</u> –0.5	+7.0	V
I <sub>IK</sub>	input clamping current	$V_I < 0 V$	-50	-	mA
I <sub>OK</sub>	output clamping current	$V_O < 0 V$	-50	-	mA
Io	output current	output in LOW-state	-	128	mA
		output in HIGH-state	-64	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		[2] -	150	°C

74LVTN16245B

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Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
P <sub>tot</sub>	total power dissipation	$T_{amb}$ = -40 °C to +85 °C			
		TSSOP48 package	[3]	500	mW
		HXQFN60 package	<u>[4]</u> _	1000	mW

- [1] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.
- [2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability.
- [3] Above 60 °C the value of Ptot derates linearly with 5.5 mW/K.
- [4] Above 70 °C the value of  $P_{tot}$  derates linearly with 1.8 mW/K.

# 8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CC}$	supply voltage		2.7	-	3.6	V
VI	input voltage		0	-	5.5	V
V <sub>IH</sub>	HIGH-level input voltage		2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage		-	-	0.8	V
I <sub>OH</sub>	HIGH-level output current		-32	-	-	mA
I <sub>OL</sub>	LOW-level output current	none	-	-	32	mA
		current duty cycle $\leq 50$ %; $f_i \geq 1 \text{ kHz}$	-	-	64	mA
T <sub>amb</sub>	ambient temperature	in free-air	-40	-	+85	°C
$\Delta t/\Delta V$	input transition rise and fall rate	outputs enabled	-	-	10	ns/V

### 9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
$T_{amb} = -4$	40 °C to +85 °C					
$V_{IK}$	input clamping voltage	$V_{CC} = 2.7 \text{ V}; I_{IK} = -18 \text{ mA}$	-1.2	-0.85	-	V
$V_{OH}$	HIGH-level output voltage	$I_{OH}$ = $-100~\mu\text{A};~V_{CC}$ = 2.7 V to 3.6 V	$V_{CC}-0.2$	$V_{CC}$	-	V
		$I_{OH} = -8 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.4	2.5	-	V
		$I_{OH} = -32 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.0	2.3	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_{CC} = 2.7 \text{ V}$				
		I <sub>OL</sub> = 100 μA	-	0.07	0.2	V
		I <sub>OL</sub> = 24 mA	-	0.3	0.5	V
		V <sub>CC</sub> = 3.0 V				
		I <sub>OL</sub> = 16 mA	-	0.25	0.4	V
		I <sub>OL</sub> = 32 mA	-	0.3	0.5	V
		I <sub>OL</sub> = 64 mA	-	0.4	0.55	V

Table 6. Static characteristics ... continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
I <sub>I</sub>	input leakage current	control pins				
		$V_{CC} = 3.6 \text{ V}; V_I = V_{CC} \text{ or GND}$	-	0.1	±1	μΑ
		$V_{CC} = 0 \text{ V or } 3.6 \text{ V}; V_{I} = 5.5 \text{ V}$	-	0.1	10	μΑ
		input/output data pins; V <sub>CC</sub> = 3.6 V	[2]			
		V <sub>I</sub> = 5.5 V	-	0.1	20	μΑ
		$V_I = V_{CC}$	-	0.5	10	μΑ
		V <sub>I</sub> = 0 V	-5	-0.1	-	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_{CC} = 0 \text{ V}$ ; $V_{I}$ or $V_{O} = 0 \text{ V}$ to 4.5 V	-	0.1	±100	μΑ
I <sub>LO</sub>	output leakage current	output in HIGH-state when $V_O > V_{CC}$ ; $V_O = 5.5 \text{ V}$ ; $V_{CC} = 3.0 \text{ V}$	-	75	125	μΑ
I <sub>O(pu/pd)</sub>	power-up/power-down output current	$V_{CC} \le 1.2 \text{ V}; V_O = 0.5 \text{ V} \text{ to } V_{CC};$ $V_I = \text{GND or } V_{CC}; n\overline{\text{OE}} = \text{don't care}$	[3] _	40	±100	μΑ
I <sub>CC</sub>	supply current	$V_{CC}$ = 3.6 V; $V_I$ = GND or $V_{CC}$ ; $I_O$ = 0 A				
		output HIGH	-	0.07	0.12	mA
		output LOW	-	4.0	6.0	mA
		outputs disabled	[4] _	0.07	0.12	mA
Δl <sub>CC</sub>	additional supply current	per input pin; $V_{CC}$ = 3.0 V to 3.6 V; one input at $V_{CC}$ – 0.6 V other inputs at $V_{CC}$ or GND	<u>[5]</u> _	0.1	0.2	mA
Cı	input capacitance	pins nDIR and $\overline{OE}$ , $V_O = 0 \text{ V or } 3.0 \text{ V}$	-	3	-	pF
$C_{io(off)}$	off-state input/output capacitance	pins nAn and nBn, outputs disabled; $V_O = \text{GND}$ or $V_{CC}$	-	9	-	pF

<sup>[1]</sup> Typical values are measured at  $V_{CC}$  = 3.3 V and at  $T_{amb}$  = 25 °C.

<sup>[2]</sup> Unused pins at  $V_{CC}$  or GND.

<sup>[3]</sup> This parameter is valid for any  $V_{CC}$  between 0 V and 1.2 V with a transition time of up to 10 ms. From  $V_{CC}$  = 1.2 V to  $V_{CC}$  = 3.3 V  $\pm$  0.3 V a transition time of 100  $\mu$ s is permitted. This parameter is valid for  $T_{amb}$  = 25 °C only.

<sup>[4]</sup>  $I_{CC}$  is measured with outputs pulled to  $V_{CC}$  or GND.

<sup>[5]</sup> This is the increase in supply current for each input at the specified voltage level other than V<sub>CC</sub> or GND.

# 10. Dynamic characteristics

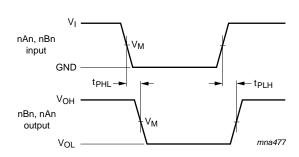
Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7.

Symbol	Parameter	Conditions	Min	Typ <mark><sup>[1]</sup></mark>	Max	Unit
$T_{amb} = -40$	°C to +85 °C					
t <sub>PLH</sub>	LOW to HIGH propagation delay	nAn to nBn or nBn to nAn; see <u>Figure 5</u>				
		V <sub>CC</sub> = 2.7 V	-	-	3.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.0	1.9	3.3	ns
t <sub>PHL</sub>	HIGH to LOW propagation delay	nAn to nBn or nBn to nAn; see <u>Figure 5</u>				
		V <sub>CC</sub> = 2.7 V	-	-	3.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.0	1.7	3.3	ns
t <sub>PZH</sub>	OFF-state to HIGH propagation delay	nOE to nAn or nBn; see <u>Figure 6</u>				
		V <sub>CC</sub> = 2.7 V	-	-	5.3	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.0	2.8	4.5	ns
t <sub>PZL</sub>	OFF-state to LOW propagation delay	nOE to nAn or nBn; see <u>Figure 6</u>				
		$V_{CC} = 2.7 \text{ V}$	-	-	5.1	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.0	2.8	4.1	ns
t <sub>PHZ</sub>	HIGH to OFF-state propagation delay	nOE to nAn or nBn; see <u>Figure 6</u>				
		V <sub>CC</sub> = 2.7 V	-	-	5.7	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.5	3.2	5.1	ns
t <sub>PLZ</sub>	LOW to OFF-state propagation delay	nOE to nAn or nBn; see <u>Figure 6</u>				
		V <sub>CC</sub> = 2.7 V	-	-	4.6	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.5	3.0	4.6	ns

<sup>[1]</sup> Typical values are measured at  $V_{CC}$  = 3.3 V and  $T_{amb}$  = 25 °C.

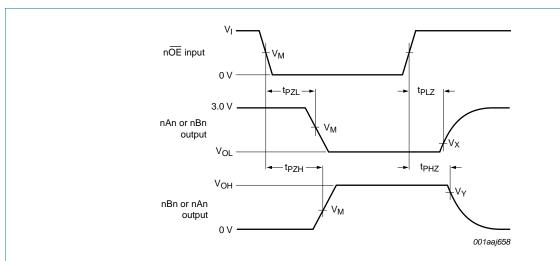
### 11. Waveforms



Measurements points are given in Table 8.

 $V_{\text{OL}}$  and  $V_{\text{OH}}$  are typical voltage output levels that occur with the output load.

Fig 5. Propagation delay input (nAn, nBn) to output (nBn, nAn)



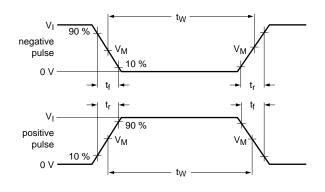
Measurements points are given in Table 8.

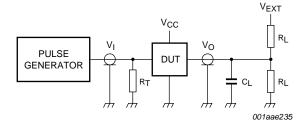
 $V_{\text{OL}}$  and  $V_{\text{OH}}$  are typical voltage output levels that occur with the output load.

Fig 6. Enable and disable times

Table 8. Measurement points

Input	Output		
$V_{M}$	V <sub>M</sub>	V <sub>X</sub>	V <sub>Y</sub>
1.5 V	1.5 V	V <sub>OL</sub> + 0.3 V	V <sub>OH</sub> – 0.3 V





Test data is given in Table 9.

Definitions test circuit:

 $R_L$  = Load resistance.

 $C_L$  = Load capacitance including jig and probe capacitance.

 $R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

 $V_{EXT}$  = External voltage for measuring switching times.

Fig 7. Test circuit for measuring switching times

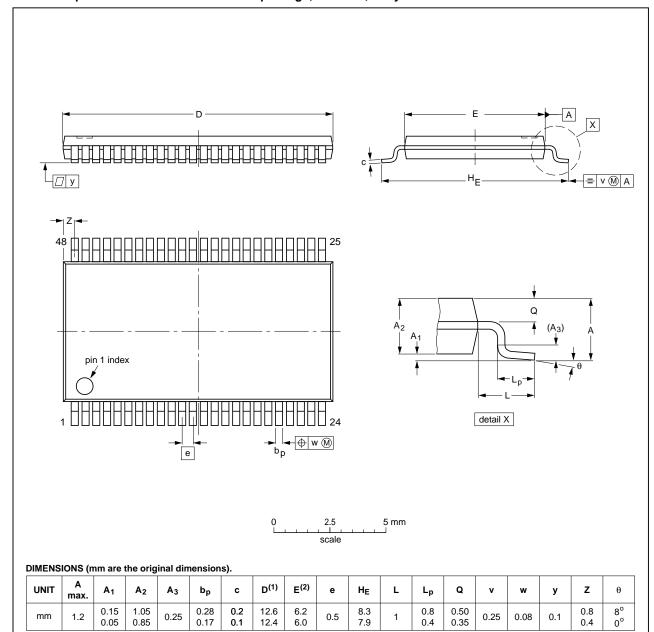
Table 9. Test data

Input			Load		V <sub>EXT</sub>			
$V_{l}$ $f_{i}$ $t_{W}$ $t_{r}$ , $t_{f}$		CL	$R_L$	t <sub>PHZ</sub> , t <sub>PZH</sub>	$t_{PLZ}$ , $t_{PZL}$	t <sub>PLH</sub> , t <sub>PHL</sub>		
2.7 V	$\leq$ 10 MHz	500 ns	$\leq$ 2.5 ns	50 pF	500 $\Omega$	GND	6 V	open

# 12. Package outline

### TSSOP48: plastic thin shrink small outline package; 48 leads; body width 6.1 mm

SOT362-1



#### Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT362-1		MO-153			<del>99-12-27</del> 03-02-19

Fig 8. Package outline SOT362-1 (TSSOP48)

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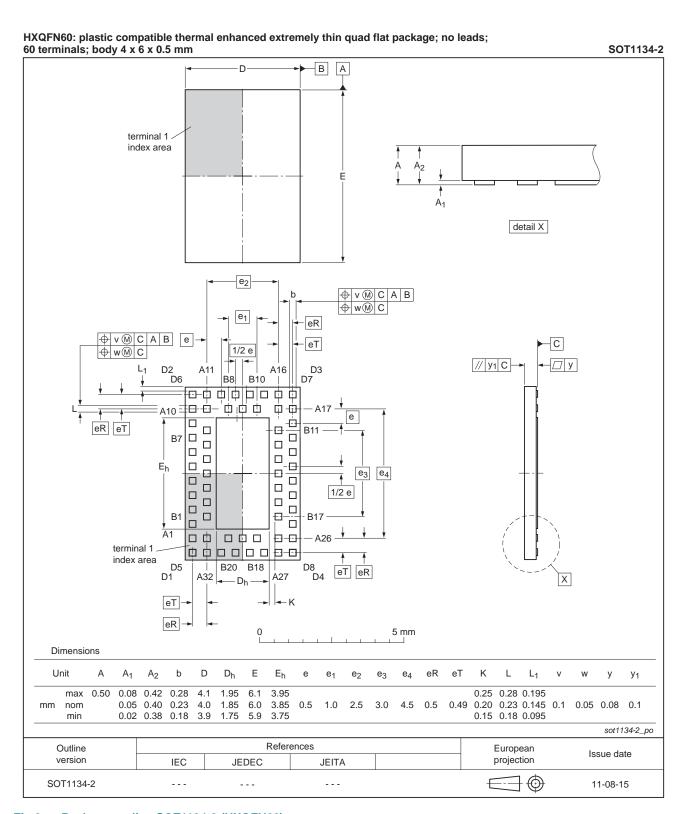


Fig 9. Package outline SOT1134-2 (HXQFN60)

### 13. Abbreviations

### Table 10. Abbreviations

Acronym	Description
BiCMOS	Bipolar Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

# 14. Revision history

### Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVTN16245B v.5	20120405	Product data sheet	-	74LVTN16245B v.4
Modifications:	<ul> <li>For type nu</li> </ul>	mber 74LVTN16245BBX th	ne SOT code has change	ed to SOT1134-2
74LVTN16245B v.4	20111122	Product data sheet	-	74LVTN16245B v.3
Modifications:	Legal pages updated.			
74LVTN16245B v.3	20110615	Product data sheet	-	74LVTN16245B v.2
74LVTN16245B v.2	20100323	Product data sheet	-	74LVTN16245B v.1
74LVTN16245B v.1	20090729	Product data sheet	-	-

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### 15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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### 17. Contents

1	General description
2	Features and benefits
3	Ordering information 1
4	Functional diagram 2
5	Pinning information 4
5.1	Pinning
5.2	Pin description 6
6	Functional description 6
7	Limiting values 6
8	Recommended operating conditions 7
9	Static characteristics 7
10	Dynamic characteristics 9
11	Waveforms
12	Package outline
13	Abbreviations 14
14	Revision history 14
15	Legal information
15.1	Data sheet status
15.2	Definitions
15.3	Disclaimers
15.4	Trademarks16
16	Contact information 16
17	Contents

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